

1. General description

Planar passivated four quadrant triac in a SOT404 (D2PAK) surface-mountable plastic package intended for use in applications requiring high bidirectional transient and blocking voltage capability and high thermal cycling performance. Typical applications include motor control, industrial and domestic lighting, heating and static switching.

2. Features and benefits

- High blocking voltage capability
- Less sensitive gate for improved noise immunity
- · Planar passivated for voltage ruggedness and reliability
- Surface-mountable package
- Triggering in all four quadrants

3. Applications

- General purpose motor control
- General purpose switching

4. Quick reference data

ick reference data						
Parameter	Conditions	N	/lin	Тур	Max	Unit
repetitive peak off- state voltage		-	-	-	600	V
non-repetitive peak on- state current	full sine wave; T _{j(init)} = 25 °C; t _p = 20 ms; <u>Fig. 4; Fig. 5</u>	-	-	-	95	A
junction temperature		-	-	-	125	°C
RMS on-state current	full sine wave; T _{mb} ≤ 99 °C; <u>Fig. 1;</u> <u>Fig. 2; Fig. 3</u>	-	-	-	12	A
eristics					1	
gate trigger current	V _D = 12 V; I _T = 0.1 A; T2+ G+; T _j = 25 °C; <u>Fig. 7</u>	-		5	35	mA
	V _D = 12 V; I _T = 0.1 A; T2+ G-; T _j = 25 °C; <u>Fig. 7</u>	-	-	8	35	mA
	Parameter repetitive peak off- state voltage non-repetitive peak on- state current junction temperature RMS on-state current	ParameterConditionsrepetitive peak off- state voltagenon-repetitive peak on- state currentfull sine wave; $T_{j(init)} = 25 \degree C$; $t_p = 20 ms; Fig. 4; Fig. 5$ junction temperatureRMS on-state currentfull sine wave; $T_{mb} \le 99 \degree C$; Fig. 1; Fig. 2; Fig. 3teristicsgate trigger current $V_D = 12 V; I_T = 0.1 A; T2+ G+;$ $T_j = 25 \degree C; Fig. 7$ $V_D = 12 V; I_T = 0.1 A; T2+ G-;$	ParameterConditionsNrepetitive peak off- state voltage-non-repetitive peak on- state currentfull sine wave; $T_{j(init)} = 25 \ ^{\circ}C$; $t_p = 20 \ ms; Fig. 4; Fig. 5-junction temperature-RMS on-state currentfull sine wave; T_{mb} \le 99 \ ^{\circ}C; Fig. 1;Fig. 2; Fig. 3-teristicsgate trigger currentV_D = 12 \ V; I_T = 0.1 \ A; T2+ \ G+;T_j = 25 \ ^{\circ}C; Fig. 7-V_D = 12 \ V; I_T = 0.1 \ A; T2+ \ G-;-$	ParameterConditionsMinrepetitive peak off- state voltage-non-repetitive peak on- state currentfull sine wave; $T_{j(init)} = 25 \ ^{\circ}C$; $t_p = 20 \ ms; Fig. 4; Fig. 5-junction temperature-RMS on-state currentfull sine wave; T_{mb} \le 99 \ ^{\circ}C; Fig. 1;Fig. 2; Fig. 3-teristicsgate trigger currentV_D = 12 \ V; I_T = 0.1 \ A; T2+ \ G+;T_j = 25 \ ^{\circ}C; Fig. 7-V_D = 12 \ V; I_T = 0.1 \ A; T2+ \ G-;-$	ParameterConditionsMinTyprepetitive peak off- state voltagenon-repetitive peak on- state currentfull sine wave; $T_{j(init)} = 25 \ ^{\circ}C$; $t_p = 20 \ ms; Fig. 4; Fig. 5junction temperatureRMS on-state currentfull sine wave; T_{mb} \le 99 \ ^{\circ}C; Fig. 1;Fig. 2; Fig. 3teristicsgate trigger currentV_D = 12 \ V; \ I_T = 0.1 \ A; \ T2+ \ G+;T_j = 25 \ ^{\circ}C; \ Fig. \ T_j = 25 \ ^{\circ}C; \ Fig. \ T_j = 0.1 \ A; \ T2+ \ G-;-8$	ParameterConditionsMinTypMaxrepetitive peak off- state voltage600non-repetitive peak on- state currentfull sine wave; $T_{j(init)} = 25 ^{\circ}C$; $t_p = 20 \text{ms}; Fig. 4; Fig. 5$ 95junction temperature125RMS on-state currentfull sine wave; $T_{mb} \le 99 ^{\circ}C$; Fig. 1; Fig. 2; Fig. 312teristicsgate trigger current $V_D = 12 ^{\circ}V; I_T = 0.1 ^{\circ}A; T2+ G+;$ $T_j = 25 ^{\circ}C; Fig. 7$ -535 $V_D = 12 ^{\circ}V; I_T = 0.1 ^{\circ}A; T2+ G-;$ -835





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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 \text{ °C}; \frac{\text{Fig. 7}}{7}$	-	10	35	mA
		V _D = 12 V; I _T = 0.1 A; T2- G+; T _j = 25 °C; <u>Fig. 7</u>	-	22	70	mA
Dynamic chara	acteristics					
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 402 V; T_j = 125 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit	100	250	-	V/µs

5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	mb	T2-T1
2	T2	main terminal 2		G sym051
3	G	gate		
mb	T2	mounting base; main terminal 2	D2PAK (SOT404)	

6. Ordering information

Table 3. Ordering information						
Type number	Package					
	Name	Description	Version			
BT138B-600	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404			

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7. Limiting values

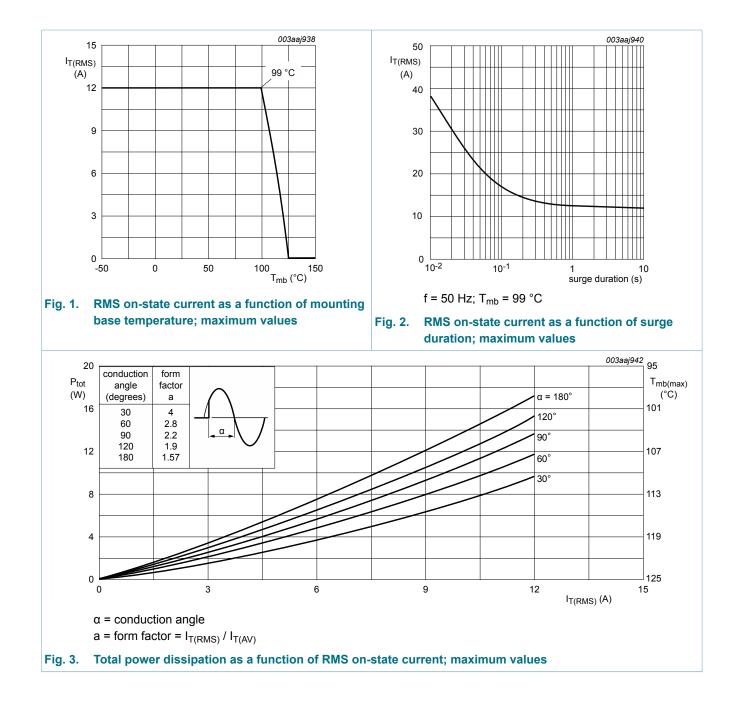
Table 4.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DRM}	repetitive peak off-state voltage		-	600	V
I _{T(RMS)}	RMS on-state current	full sine wave; $T_{mb} \le 99$ °C; Fig. 1; Fig. 2; Fig. 3	-	12	A
I _{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25 \text{ °C};$ $t_p = 20 \text{ ms}; \frac{\text{Fig. 4}}{25}; \text{ Fig. 5}$	-	95	A
		full sine wave; $T_{j(init)}$ = 25 °C; t_p = 16.7 ms	-	105	A
l ² t	I ² t for fusing	t _p = 10 ms; sine-wave pulse	-	45	A ² s
dl _T /dt r	rate of rise of on-state current	I_T = 20 A; I_G = 0.2 A; dI_G/dt = 0.2 A/µs; T2+ G+	-	50	A/µs
		I_T = 20 A; I_G = 0.2 A; dI_G/dt = 0.2 A/µs; T2+ G-	-	50	A/µs
		I_T = 20 A; I_G = 0.2 A; dI_G/dt = 0.2 A/µs; T2- G-	-	50	A/µs
		I_T = 20 A; I_G = 0.2 A; dI_G/dt = 0.2 A/µs; T2- G+	-	10	A/µs
I _{GM}	peak gate current		-	2	А
P _{GM}	peak gate power		-	5	W
P _{G(AV)}	average gate power	over any 20 ms period	-	0.5	W
T _{stg}	storage temperature		-40	150	°C
Tj	junction temperature		-	125	°C

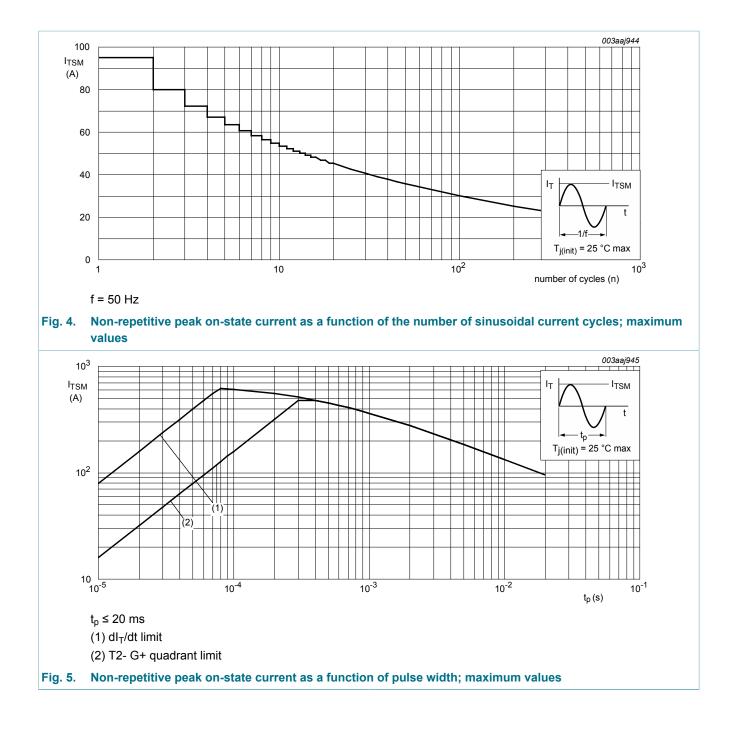
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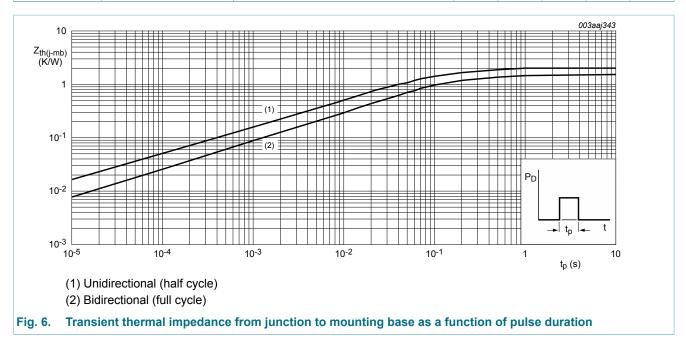
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8. Thermal characteristics

Table 5. Th	nermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f	thermal resistance	full cycle; <u>Fig. 6</u>	-	-	1.5	K/W
	from junction to mounting base	half cycle; <u>Fig. 6</u>	-	-	2	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	minimum footprint: FR4 board	-	55	-	K/W



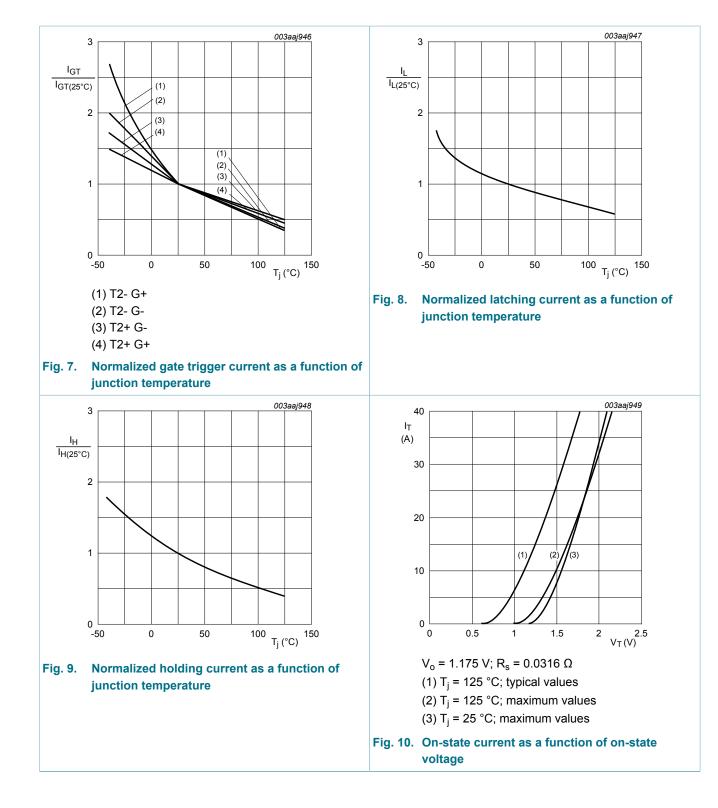
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9. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
I _{GT}	gate trigger current	V_D = 12 V; I _T = 0.1 A; T2+ G+; T _j = 25 °C; <u>Fig. 7</u>	-	5	35	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ T2+ G-};$ T _j = 25 °C; Fig. 7	-	8	35	mA
		V _D = 12 V; I _T = 0.1 A; T2- G-; T _j = 25 °C; <u>Fig. 7</u>	-	10	35	mA
		V _D = 12 V; I _T = 0.1 A; T2- G+; T _j = 25 °C; <u>Fig. 7</u>	-	22	70	mA
I _L latching current	latching current	V_D = 12 V; I _G = 0.1 A; T2+ G+; T _j = 25 °C; <u>Fig. 8</u>	-	7	40	mA
		$V_D = 12 \text{ V}; \text{ I}_G = 0.1 \text{ A}; \text{ T2+ G-};$ T _j = 25 °C; Fig. 8	-	20	60	mA
		$V_D = 12 \text{ V}; \text{ I}_G = 0.1 \text{ A}; \text{ T2- G-};$ T _j = 25 °C; Fig. 8	-	8	40	mA
		$V_D = 12 \text{ V}; \text{ I}_G = 0.1 \text{ A}; \text{ T2- G+};$ T _j = 25 °C; Fig. 8	-	10	60	mA
н	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u>	-	6	30	mA
/ _T	on-state voltage	I _T = 15 A; T _j = 25 °C; <u>Fig. 10</u>	-	1.4	1.65	V
/ _{GT}	gate trigger voltage	V _D = 12 V; I _T = 0.1 A; T _j = 25 °C; Fig. 11	-	0.7	1	V
		V _D = 400 V; I _T = 0.1 A; T _j = 125 °C; Fig. 11	0.25	0.4	-	V
D	off-state current	V _D = 600 V; T _j = 125 °C	-	0.1	0.5	mA
Dynamic cl	naracteristics	· · · · · · · · · · · · · · · · · · ·				
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 402 V; T _j = 125 °C; (V _{DM} = 67% of V _{DRM}); exponential waveform; gate open circuit	100	250	-	V/µs
lgt	gate-controlled turn-on time	I _{TM} = 16 A; V _D = 600 V; I _G = 0.1 A; dI _G / dt = 5 A/µs	-	2	-	μs

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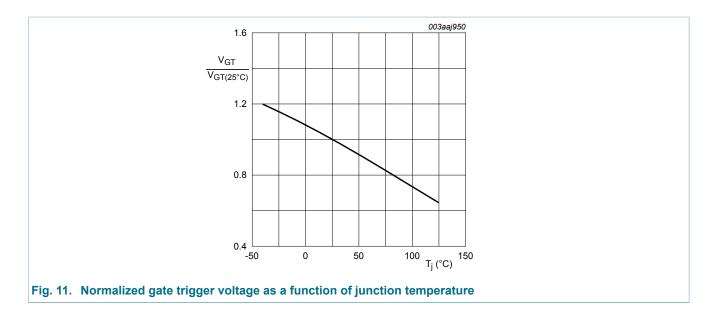


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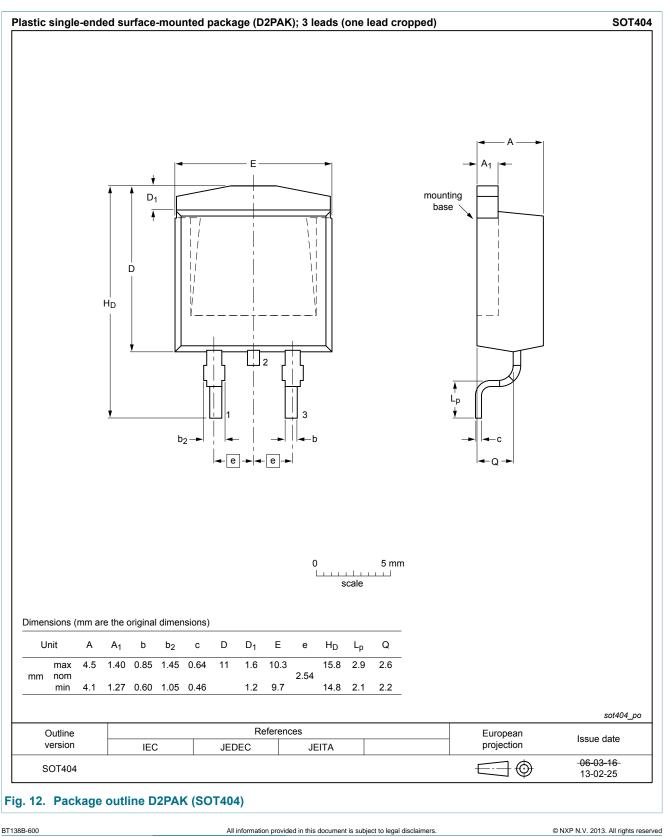
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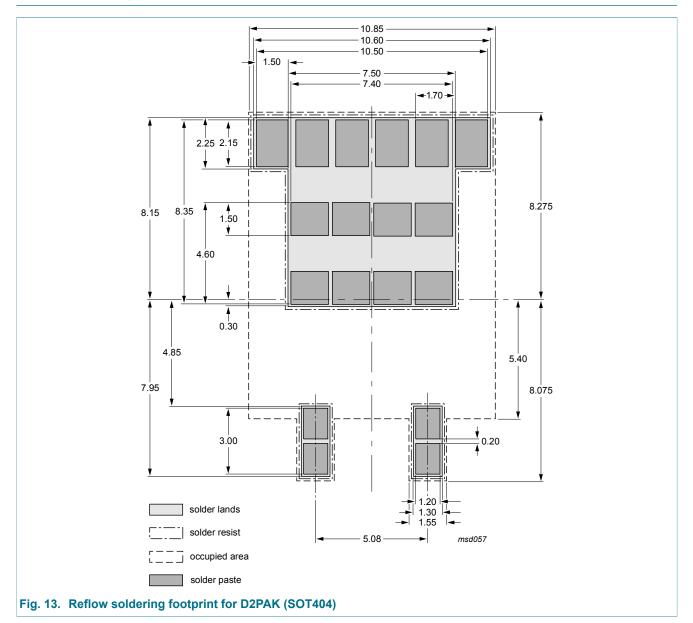
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10. Package outline



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11. Soldering



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12. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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